

JSAP-KPS Joint Symposium - Wide Bandgap Semiconductor Devices -

Wide bandgap semiconductor devices have been studied energetically, and the importance to solve the environmental and energy problems on the earth is increasing. To solve the global problems, cooperation among countries is crucial. In this symposium, active researchers in the field of wide bandgap semiconductor devices are invited from Japan and Korea that have been developed the field of electronic devices in East Asia. The current research activities are introduced, and the cooperation between JSAP and KPS is deepened in the symposium.

Date and time September 19 (Wed.) 9:00 –15:00

Venue / Language Nagoya congress center / English

Invited speakers

From Japan Society of Applied Physics(JSAP) From Korean Physical Society(KPS)

Takuji Hosoi (Osaka Univ.)
"Challenges in SiO₂/SiC interface passivation for SiC power MOSFET"

Jae Su Yu (Kyunghee Univ.)
"Wide band gap metal oxide materials for sensing and renewable energy applications"

Kazutoshi Kojima (AIST)
"Challenges in 4H-SiC crystal growth and epitaxy for ultra-high voltage device applications"

Jong-Won Lim (ETRI)
"Status of GaN power transistor and MMICs in ETRI"

Masamichi Akazawa (Hokkaido Univ.)
"Investigation of lightly Mg-ion-implanted GaN using MOS structure"

Jong Kyu Kim (POSTECH)
"Enhanced light extraction from AlGaIn deep ultraviolet LEDs"

Manato Deki (Nagoya Univ.)
"Crystal plane dependence of interface states density in c-and m-plane GaN MOS capacitors"

Yong-Hoon Cho (KAIST)
"Classical and quantum light generation from GaN-based semiconductor nanostructures"

Committees

Let's join the symposium ! !

13.7 Compound and power electron devices and process technology:
JSAP Masashi Kato, Taketomo Sato, Kozo Makiyama, Kenji Shiojima
Solid state physics and applications subcommittee:
Toshiharu Kubo, Hideto Miyake, Naoki Shigekawa, Seiji Nakamura
KPS Dankook University: Yongmin Kim